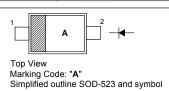
SILICON EPITAXIAL PLANAR DIODE

Fast Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	80	V
Average Rectified Output Current	I _O	125	mA
Forward Continuous Current	I _{FM}	250	mA
Non-Repetitive Peak Forward Surge Current (at t = 1 μs)	I _{FSM}	0.5	А
Power Dissipation	P _d	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 5 mA at I_F = 10 mA at I_F = 100 mA at I_F = 150 mA	V _F	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Leakage Current at V_R = 80 V at V_R = 20 V at V_R = 75 V, T_J = 150 °C at V_R = 25 V, T_J = 150 °C	I _R	- - -	100 25 50 30	nA nA µA µA
Reverse Breakdown Voltage at $I_R = 100 \mu A$	V _{(BR)R}	80	-	V
Capacitance at $V_R = 0.5 \text{ V}$, $f = 1 \text{ MHz}$	C _{tot}	-	4	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{rr} = 0.1$ X I_R , $R_L = 100$ Ω	t _{rr}	-	4	ns





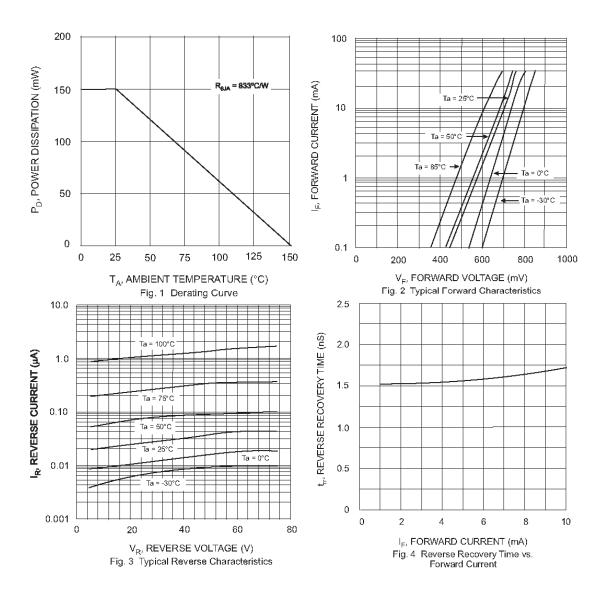






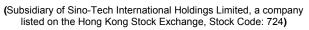


Dated: 07/04/2009















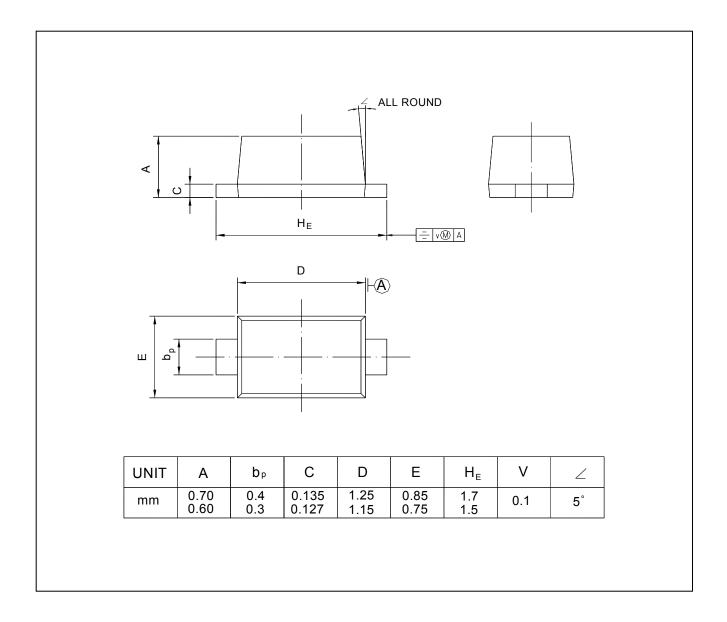




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523





SEMTECH ELECTRONICS LTD.









